

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Divisional Application of)
Shunpei YAMAZAKI et al.)
Based On Application No. 09/838,216) Art Unit: 2824
Which Was Filed: April 20, 2001) Examiner: M. Lebentritt
For: METHOD FOR FABRICATING)
SEMICONDUCTOR THIN FILM) Date: October 6, 2003

INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

In accordance with the duty of disclosure as set forth in 37 C.F.R. §1.56, Applicants hereby submit the following information in conformance with 37 C.F.R. §§ 1.97 and 1.98. Pursuant to 37 C.F.R. § 1.98, copies of some of the documents cited are enclosed.

The references listed on the attached Form PTO-1449 were cited in parent application Serial No. 09/838,216 filed April 20, 2001, and its predecessor application Serial Nos. 09/115,838 and 08/536,977, from which priority is claimed under 35 U.S.C. 120.

It is requested that the accompanying PTO-1449 be considered and made of record in the above-identified application. To assist the Examiner, the documents are listed on the attached form PTO-1449. It is respectfully requested that an Examiner initialed copy of this form be returned to the undersigned.

Respectfully submitted,

By: _____


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Substitute for form 1449A/PTO				Complete if Known	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(use as many sheets as necessary)</i>				Application Number	New Application
				Filing Date	October 6, 2003
				First Named Inventor	Shunpei YAMAZAKI et al.
				Art Unit	2824
				Examiner Name	M. Lebentritt
Sheet	1	of	2	Attorney Docket Number	740756-2659

U.S. PATENT DOCUMENTS					
Examiner Initials ⁵	Cite No. ¹	U.S. Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number - Kind Code ² (if known)			
		US-5,700,333	12/23/1997	Yamazaki et al.	
		US-4,561,171	12/31/1985	Schlosser	
		US-5,147,826	09/15/1992	Liu et al.	
		US-5,229,306	07/20/1993	Lindberg	
		US-5,244,819	09/14/1993	Yue	
		US-5,275,851	01/04/1994	Fonash et al.	
		US-5,441,899	08/15/1995	Nakai	
		US-5,444,001	08/22/1995	Tokuyama	
		US-5,529,937	06/25/1996	Zhang	
		US-5,696,011	12/09/1997	Nakata et al.	
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		US-6,048,758	04/11/2000	Yamazaki et al.	

FOREIGN PATENT DOCUMENTS						
Examiner Initials ⁵	Cite No. ¹	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁶
		Country Code ³ Number ⁴ Kind Code ⁵ (if known)				
		JP6333824	12/02/1994			Abstract
		JP6333825	12/02/1994			Full & Abstract
		JP 03-229415	10/11/1991			Abstract
		JP 06-333824	12/02/1994			Abstract

OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS			
Examiner Initials ⁵	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
		DVURECHENSKII.A, TRANSPORT PHENOMENA IN AMORPHOUS SILICON DOPED BY ION IMPLANTATION OF 3D METALS, PP.635-64OPHYS. STAT. SOL.	
		HAYZELDEN.C, IN SITU TRANSMISSION ELECTRON MICROSCOPY STUDIES OF SILICIDE-MEDIATED CRYSTALLIZATION OF AMORPHOUS SILICON, VOL.60/PP.225-227APPL. PHYS. LETT.	
		HEMPEL.T, NEEDLE-LIKE CRYSTALLIZATION OF NI DOPED AMORPHOUS SILICON THIN FILMS, VOL.85/PP.921-92450LID STATE COMMUNICATIONS	
		KAKKAD.R, CRYSTALLIZED SI FILMS BY LOW-TEMPERATURE RAPID THERMAL ANNEALING OF AMORPHOUS SILICON, VOL. 65/PP. 2069-2072J. APPL. PHYS.	
		KAKKAD.R, LOW TEMPERATURE SELECTIVE CRYSTALLIZATION OF AMORPHOUS SILICON, VOL. 115IPP.66-68JOURNAL OF NON-CRYSTALLINE SOLIDS	

Examiner Signature		Date Considered	
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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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				Application Number		New Application	
				Filing Date		October 6, 2003	
				First Named Inventor		Shunpei YAMAZAKI et al.	
				Art Unit		2854	
Examiner Name		M. Lebentritt					
Attorney Docket Number		740756-2659					
Sheet	2	of	2				

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		Number - Kind Code ² (if known)			
		US-5,789,284	08/1998	Yamazaki et al.	
		US-6,331,457	12/2001	Yamazaki et al.	
		US-6,218,219	04/2001	Yamazaki et al.	
		US-6,197,624	03/2001	Yamazaki	
		US-6,048,758	04/2000	Yamazaki et al.	
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		US-2001/0041397	05/2001	Fukushima	
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		LIU.G, SELECTIVE AREA CRYSTALLIZATION OF AMORPHOUS SILICON FILMS BY LOW-TEMPERATURE RAPID THERMAL ANNEALING, VOL.551PP.660-662APPL. PHYS. LETT.	
		LIU.G, "POLYCRYSTALLINE SILICON THIN FILM TRANSISTORS ON CORNING 7059 GLASS SUBSTRATES USING SHORT TIME, VOL. 62/PP.2554-2556APPL. PHYS. LETT.	

Examiner Signature		Date Considered	
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